DATA SHEET



MOS FIELD EFFECT TRANSISTOR 2SK3113B

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3113B is N-channel MOS FET device that features a low gate charge and excellent switching characteristics, and designed for high voltage applications such as switching power supply, AC adapter.

FEATURES

• Low on-state resistance

 $R_{DS(on)} = 4.4 \Omega MAX. (V_{GS} = 10 V, I_{D} = 1.0 A)$

Low gate charge

 $Q_G = 7.9 \text{ nC TYP.}$ ($V_{DD} = 450 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 2.0 \text{ A}$)

• Gate voltage rating: ±30 V

Avalanche capability ratings

<R> ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE	
2SK3113B-S15-AY Note	Dura On (Tin)	Tube 70 p/tube	TO-251 (MP-3-a) typ. 0.39 g	
2SK3113B(1)-S27-AY Note		Tube 75 p/tube	TO-251 (MP-3-b) typ. 0.34 g	
2SK3113B-ZK-E1-AY Note	Pure Sn (Tin)	Tape 2500 p/reel	TO 050 (MD 07/4) by 0.07 m	
2SK3113B-ZK-E2-AY Note			TO-252 (MP-3ZK) typ. 0.27 g	

Note Pb-free (This product does not contain Pb in external electrode.)

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

ABSOLUTE IVIANIIVIUIVI KATINGS (T	A - 25 C)		
Drain to Source Voltage (VGS = 0 V)	VDSS	600	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±30	V
Drain Current (DC) (Tc = 25°C)	I _{D(DC)}	±2.0	Α
Drain Current (pulse) Note1	D(pulse)	±8.0	Α
Total Power Dissipation (Tc = 25°C)	P _{T1}	20	W
Total Power Dissipation (T _A = 25°C) Note2	P _{T2}	1.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C
Single Avalanche Current Note3	las	2.0	Α
Single Avalanche Energy Note3	Eas	2.7	mJ

(TO-251)



(TO-252)



Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

- 2. Mounted on glass epoxy board of 40 mm × 40 mm × 1.6 mm
- 3. Starting T_{ch} = 25°C, V_{DD} = 150 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V

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The mark <R> shows major revised points.

The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.

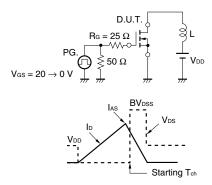
Printed in Japan

ELECTRICAL CHARACTERISTICS (TA = 25°C)

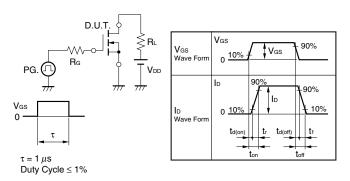
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	Ipss	V _{DS} = 600 V, V _{GS} = 0 V			100	μA
Gate Leakage Current	Igss	V _{GS} = ±30 V, V _{DS} = 0 V			±10	μА
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	2.5		3.5	V
Forward Transfer Admittance Note	yfs	V _{DS} = 10 V, I _D = 1.0 A	0.5	0.9		S
Drain to Source On-state Resistance Note	R _{DS(on)}	V _{GS} = 10 V, I _D = 1.0 A		3.2	4.4	Ω
Input Capacitance	Ciss	V _{DS} = 10 V		290		pF
Output Capacitance	Coss	V _{GS} = 0 V		75		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		7		pF
Turn-on Delay Time	t d(on)	V _{DD} = 150 V, I _D = 1.0 A		10.5		ns
Rise Time	tr	V _{GS} = 10 V		4.8		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		15.8		ns
Fall Time	tr	R _L = 10 Ω		10.5		ns
Total Gate Charge	Q _G	V _{DD} = 450 V		7.9		nC
Gate to Source Charge	Qgs	V _{GS} = 10 V		2.7		nC
Gate to Drain Charge	Q _{GD}	I _D = 2.0 A		3.2		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 2.0 A, V _{GS} = 0 V		0.8		V
Reverse Recovery Time	trr	I _F = 2.0 A, V _{GS} = 0 V		190		ns
Reverse Recovery Charge	Qrr	di/dt = 50 A/μs		500		nC

Note Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY



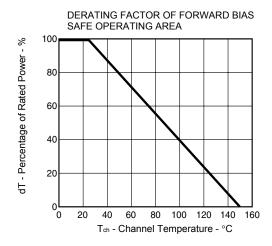
TEST CIRCUIT 2 SWITCHING TIME

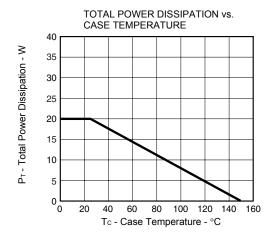


TEST CIRCUIT 3 GATE CHARGE

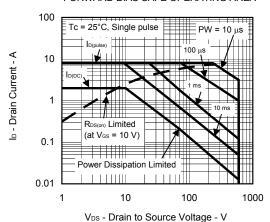
$$\begin{array}{c|c} D.U.T. \\ \hline \\ IG = 2 \text{ mA} \\ \hline \\ PG. \\ \hline \\ \end{array}$$

TYPICAL CHARACTERISTICS (TA = 25°C)

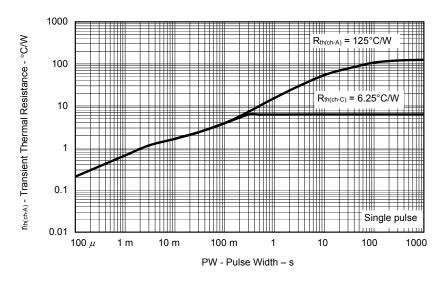




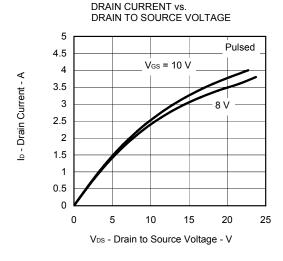
FORWARD BIAS SAFE OPERATING AREA

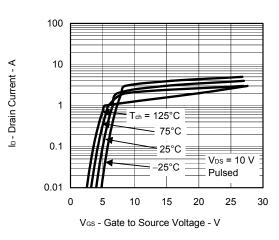


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

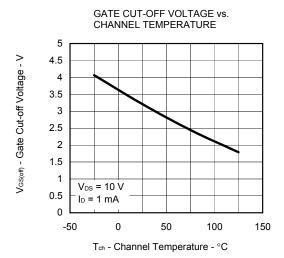


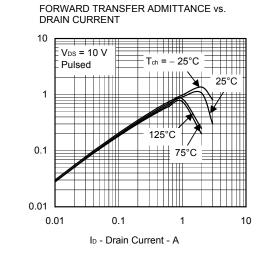
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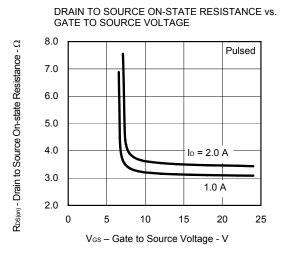


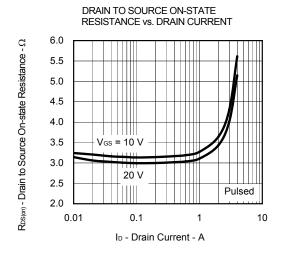


FORWARD TRANSFER CHARACTERISTICS



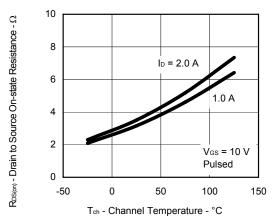




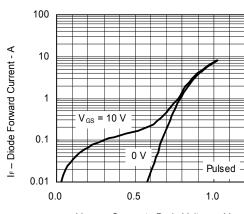


| yfs | - Forward Transfer Admittance - S

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

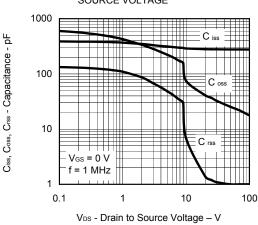


SOURCE TO DRAIN DIODE FORWARD VOLTAGE

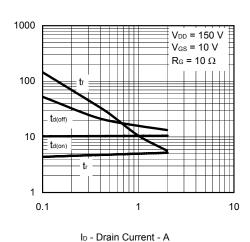


V_{F(S-D)} – Source to Drain Voltage - V

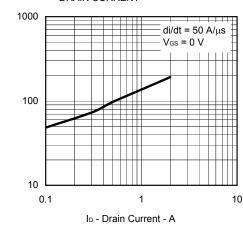
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



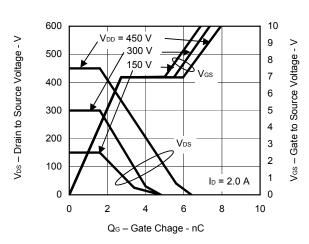
SWITCHING CHARACTERISTICS



REVWESE RECOVERY TIME vs. DRAIN CURRENT



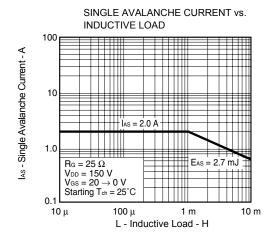
DYNAMIC INPUT/OUTPUT CHARACTERISTICS

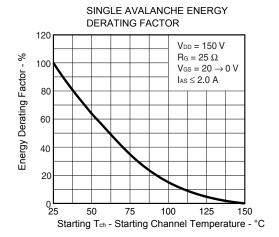


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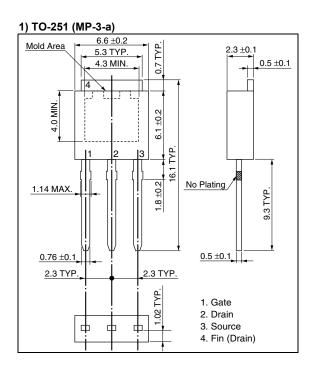
ta(on), tr, ta(off), tr - Switching Time - ns

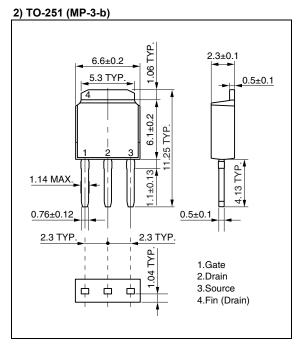
trr - Reverse Recovery Time - ns



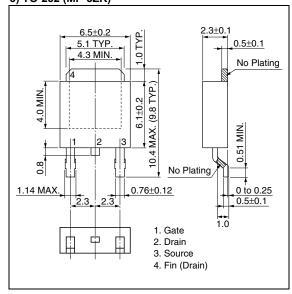


<R> PACKAGE DRAWINGS (Unit: mm)

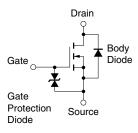




3) TO-252 (MP-3ZK)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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